**Product data sheet** 

# 1. General description

Planar passivated very sensitive gate four quadrant triac in a TO92 plastic package. This very sensitive gate "series D" triac is intended for interfacing with low power drivers including microcontrollers.

### 2. Features and benefits

- · High blocking voltage capability
- · Very sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- Direct interfacing to logic level ICs
- · Direct interfacing with low power gate drivers and microcontrollers

## 3. Applications

- General purpose low power motor control
- · General purpose switching and phase control
- · Air conditioner indoor fan control

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Absolute maximum rating							
$V_{DRM}$	repetitive peak off-state voltage			-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 51.2 °C; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	1	А
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig. 4; Fig. 5		-	-	12.5	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 16.7 \text{ms}$		-	-	13.7	Α
T <sub>j</sub>	junction temperature			-	-	125	°C
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$		-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 7}$		-	-	5	mA
ı		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	7	mA

I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>		-	1.3	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>		-	1.2	1.5	V
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Dynamic	Dynamic characteristics						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_{j}$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 k $\Omega$		20	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; dI_{com}/dt = 0.5 \text{ A/ms};$ $I_T = 1 \text{ A}; gate open circuit}$		3	-	-	V/µs

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T2	main terminal 2		
2	G	gate	<u> </u>	T2—T1
3	T1	main terminal 1		sym051

# 6. Ordering information

**Table 3. Ordering information** 

Table of Grading									
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date			
BT131-800D	TO92	BT131-600D,112	Bulk	1000	SOT54	14-Nov-2013			
BT131-800D	TO92	BT131-600D,412	Bulk	1000	SOT54	14-Nov-2013			
BT131-800D	TO92	BT131-600D,116	Reel	2000	SOT54	14-Nov-2013			
BT131-800D/L01	TO92	BT131-600D/L01EP	Bulk	500	SOT54/L01	14-Nov-2013			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking codes
BT131-800D	131-8D

# 8. Limiting values

### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
repetitive peak off-state voltage			-	800	V
RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 51.2 °C; <u>Fig 1</u> ; <u>Fig 2</u> ; <u>Fig 3</u>		-	1	А
non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 20 ms; Fig 4; Fig 5		-	12.5	А
	full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms		-	13.7	Α
I <sup>2</sup> t for fusing	t <sub>P</sub> = 10 ms; SIN		-	0.78	A <sup>2</sup> s
rate of rise of on-state current	I <sub>G</sub> = 10 mA		-	50	A/µs
	I <sub>G</sub> = 10 mA		-	50	A/µs
	I <sub>G</sub> = 10 mA		-	50	A/µs
	I <sub>G</sub> = 14 mA		-	10	A/µs
peak gate current			-	2	Α
peak gate power			-	5	W
average gate power	over any 20 ms period		-	0.1	W
storage temperature			-40	150	°C
junction temperature			-	125	°C
	repetitive peak off-state voltage  RMS on-state current  non-repetitive peak onstate current  I²t for fusing  rate of rise of on-state current  peak gate current  peak gate power  average gate power  storage temperature	repetitive peak off-state voltage  RMS on-state current  full sine wave; $T_{lead} \le 51.2 ^{\circ}\text{C}$ ; Fig 1; Fig 2; Fig 3  non-repetitive peak onstate current  full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 20 ^{\circ}\text{ms}$ ; Fig 4; Fig 5  full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ; $t_p = 16.7 ^{\circ}\text{ms}$ I²t for fusing $t_p = 10 ^{\circ}\text{ms}$ ; SIN  rate of rise of on-state current $I_G = 10 ^{\circ}\text{mA}$ $I_G = 10 ^{\circ}\text{mA}$ $I_G = 10 ^{\circ}\text{mA}$ $I_G = 14 ^{\circ}\text{mA}$ peak gate current  peak gate power  average gate power  storage temperature	repetitive peak off-state voltage  RMS on-state current  full sine wave; $T_{lead} \le 51.2  ^{\circ}\text{C}$ ; Fig 1; Fig 2; Fig 3  non-repetitive peak onstate current  full sine wave; $T_{l(init)} = 25  ^{\circ}\text{C}$ ; $t_p = 20  \text{ms}$ ; Fig 4; Fig 5  full sine wave; $T_{l(init)} = 25  ^{\circ}\text{C}$ ; $t_p = 16.7  \text{ms}$ I 2t for fusing $t_p = 10  \text{ms}$ ; SIN  rate of rise of on-state current $l_G = 10  \text{mA}$ $l_G = 10  \text{mA}$ $l_G = 10  \text{mA}$ $l_G = 10  \text{mA}$ peak gate current  peak gate power  average gate power  storage temperature	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

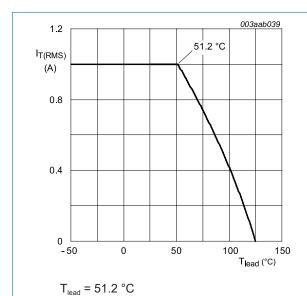


Fig. 1. RMS on-state current as a function of lead temperature; maximum values

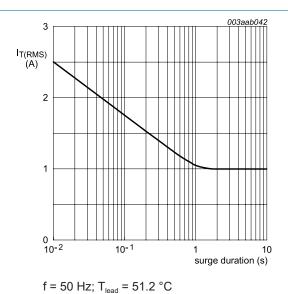
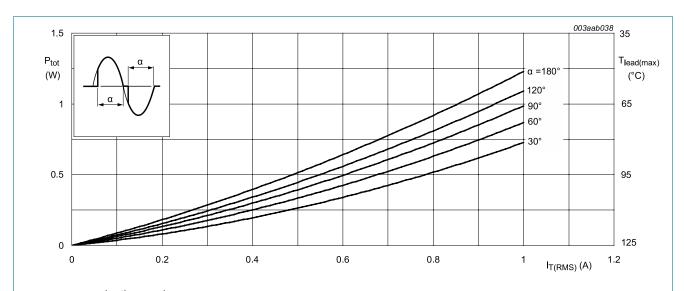
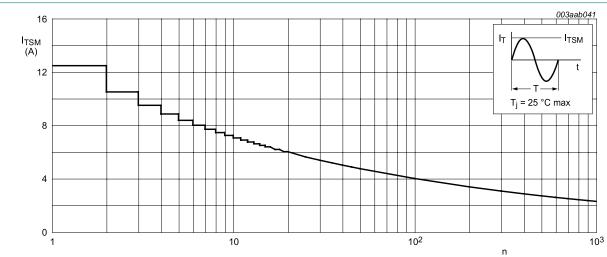


Fig. 2. RMS on-state current as a function of surge duration; maximum values



 $\alpha$  = conduction angle

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

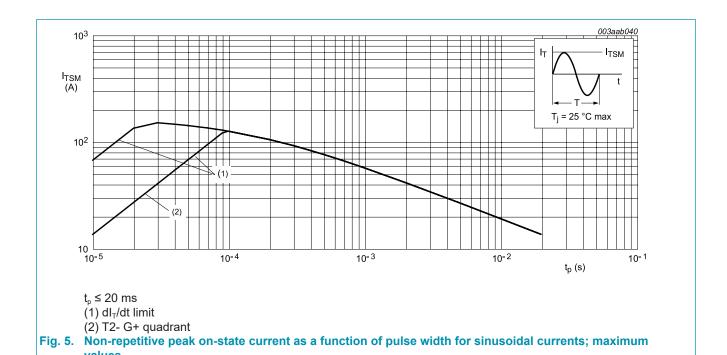


f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

WeEn Semiconductors BT131-800D

**4Q Triac** 



## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance	full cycle; Fig 6	-	-	60	K/W
	from junction to lead	half cycle; <u>Fig 6</u>	-	-	80	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

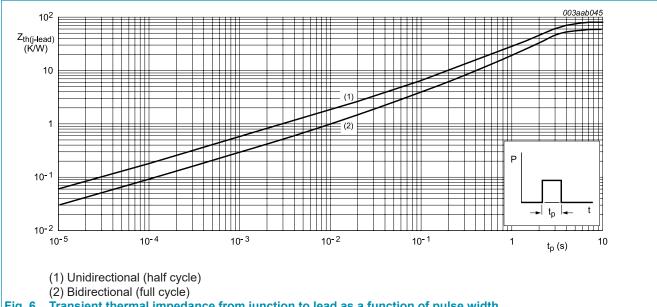
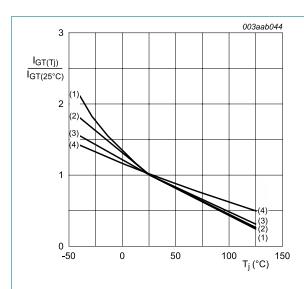


Fig. 6. Transient thermal impedance from junction to lead as a function of pulse width

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					'
$I_{\text{GT}}$	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G-;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	7	mA
I <sub>L</sub> la	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 8$	-	-	20	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 8}$	-	-	10	mA
I <sub>H</sub>	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; Fig. 9$	-	1.3	10	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1.4 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.2	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.7	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C}$	0.2	0.3	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; $R_{GT1(ext)}$ = 1 kΩ	20	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; $T_j$ = 125 °C; $dI_{com}/dt$ = 0.5 A/ms; $I_T$ = 1 A; gate open circuit	3	-	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM} = 1.5 \text{ A}; V_D = 800 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$	-	2	-	μs



- (1) T2- G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

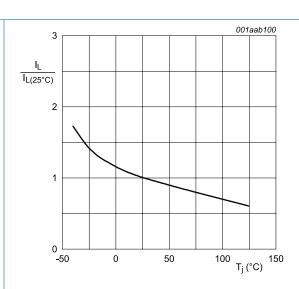


Fig. 8. Normalized latching current as a function of junction temperature

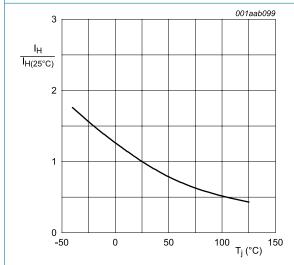
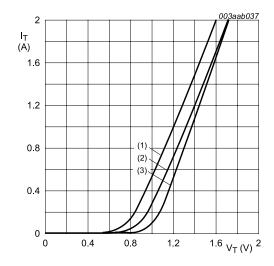


Fig. 9. Normalized holding current as a function of junction temperature



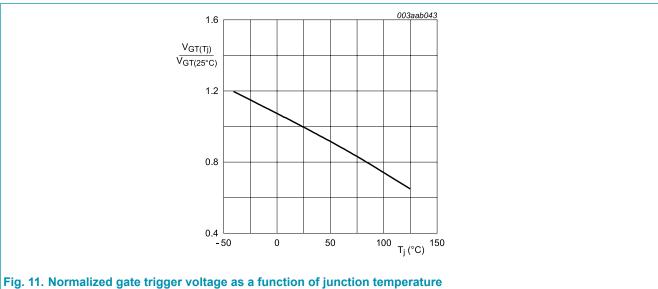
 $V_o$  = 0.92 V;  $R_s$  = 0.4  $\Omega$ (1)  $T_j$  = 125 °C; typical values (2)  $T_j$  = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

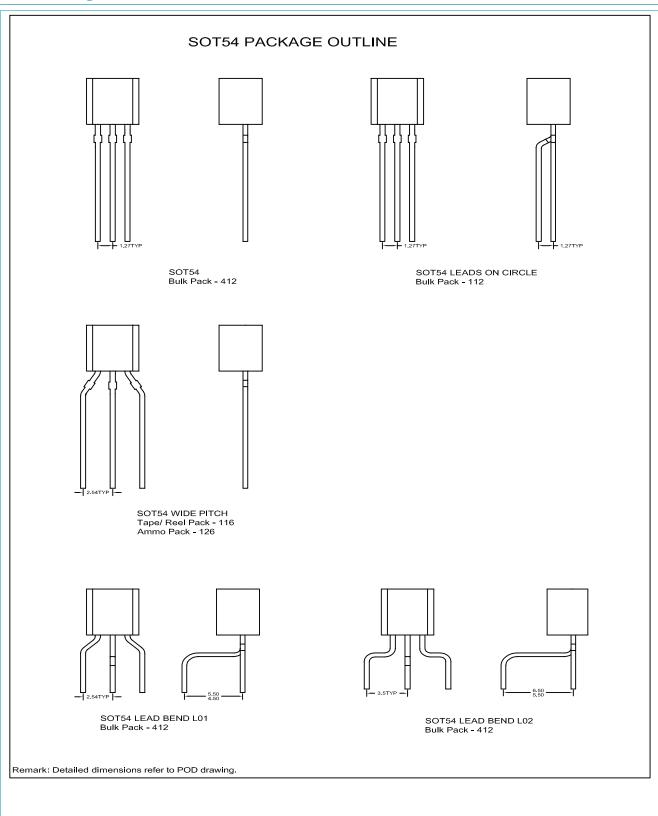
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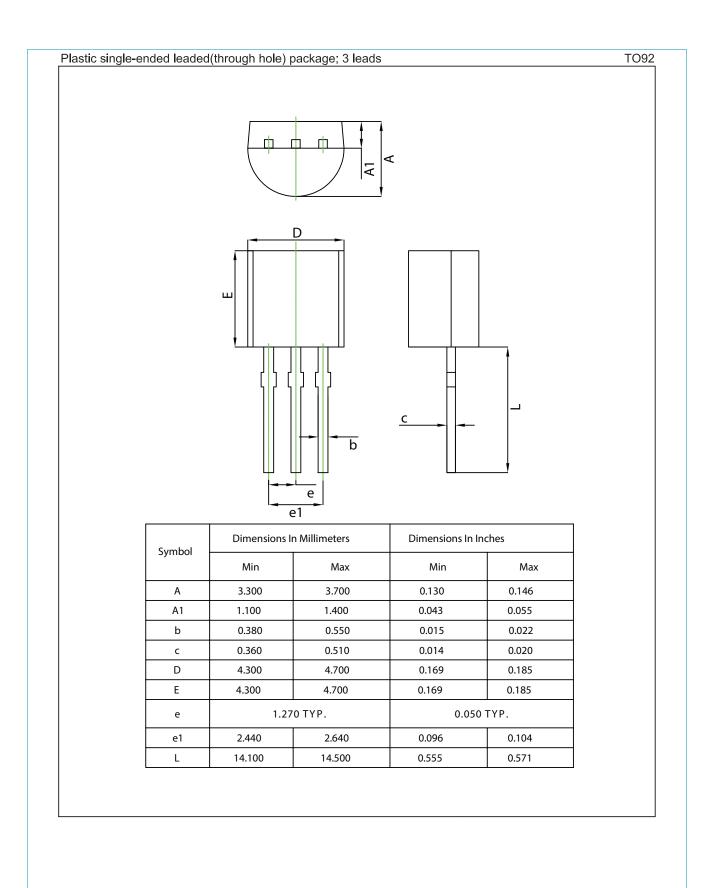
**4Q Triac** 



1 19. 11. Normanzed gate trigger voltage as a function of junction temperature

# 11. Package outline





4Q Triad

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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For more information, please visit: http://www.ween-semi.com For sales office addresses, please send an email to: salesaddresses@ween-semi.com Date of release: 19 October 2021

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